



WANSEMI
万芯半导体

WP2302AS3

Enhancement Mode N-Channel Power MOSFET

SOT23-3/NMOS/20V/ ± 12 V/0.7V/3.2A/35m Ω

Rev1.2

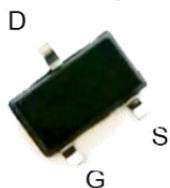
20V, 35mΩ, 3.2A, N-Channel MOSFET

1.Features

- ◆ Advanced Trench Technology
- ◆ Surface mount package

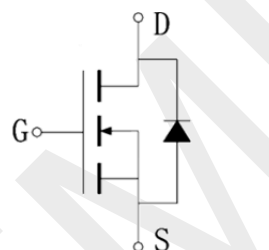
2.Applications

- ◆ Power Management
- ◆ Load Switching



SOT23-3

Pin Description



Schematic Diagram

V_{DS}	$R_{DS(on)}$ Typ.	I_D
20V	35mΩ @ 4.5V	3.2A
	42.5mΩ @ 2.5V	

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP2302AS3	A2SHB	SOT23-3	3,000	180,000

4.Absolute Max Ratings at Ta=25°C (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	20	V
Gate to Source Voltage	V_{GSS}	±12	V
Drain Current (DC)	I_D	3.2	A
Drain Current (Pulse), $PW \leq 300\mu s$	I_{DP}	12	A
Total Dissipation	P_D	0.6	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

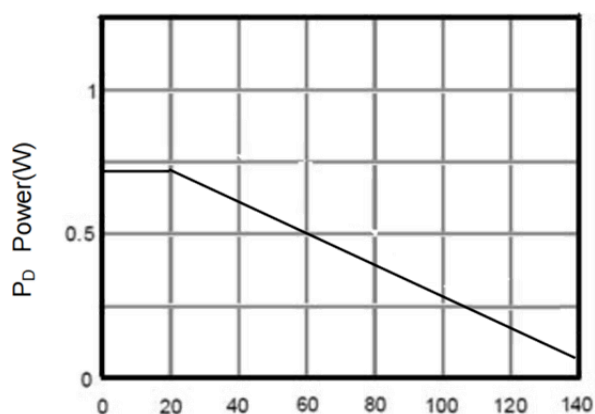
Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5. Electrical Characteristics at Ta=25°C (Note 2)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	20	22		V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	0.4	0.7	1.2	V
Forward Transconductance	G_{FS}	$I_D = 3.2A, V_{DS} = 5V$		10		S
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 3.2A, V_{GS} = 4.5V$		35	40	m Ω
		$I_D = 2A, V_{GS} = 2.5V$		42.5	52	m Ω
Input Capacitance	C_{iss}	$V_{GS}=0V,$		340		pF
Output Capacitance	C_{oss}	$V_{DS}=10V,$		115		pF
Reverse Transfer Capacitance	C_{rss}	Frequency=1.0MHz		33		pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 3A,$ $R_G = 6\Omega, V_{GEN} = 4.5V, R_L = 5.5\Omega$		12		ns
Rise Time	t_r			36		ns
Turn-OFF Delay Time	$t_{d(off)}$			34		ns
Fall Time	t_f			10		ns
Total Gate Charge	Q_g	$V_{DS} = 10V,$		5.4		nC
	Q_{gs}	$V_{GS} = 4.5V,$		0.7		nC
	Q_{gd}	$I_D = 3A$		1.6		nC
Diode Forward Voltage	V_{FSD}	$I_{SD} = 3.2A, V_{GS} = 0$	0.5	0.86	1.2	V

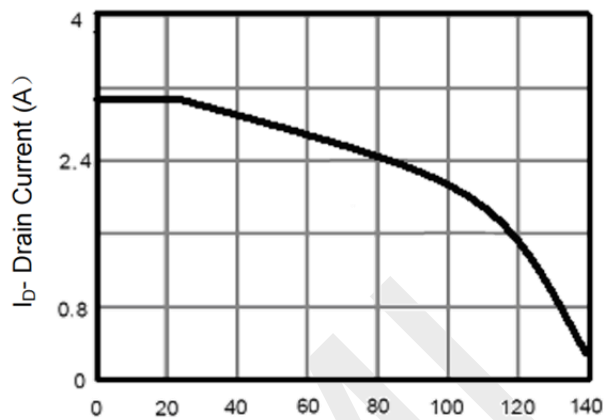
Note 2: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Typical Electrical and Thermal Characteristics



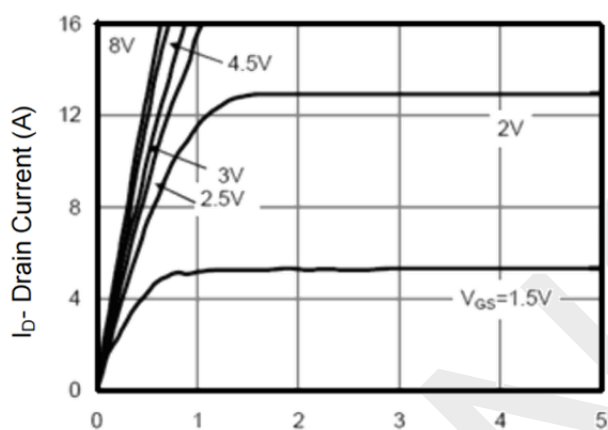
T_J -Junction Temperature (°C)

Typical Output Characteristics



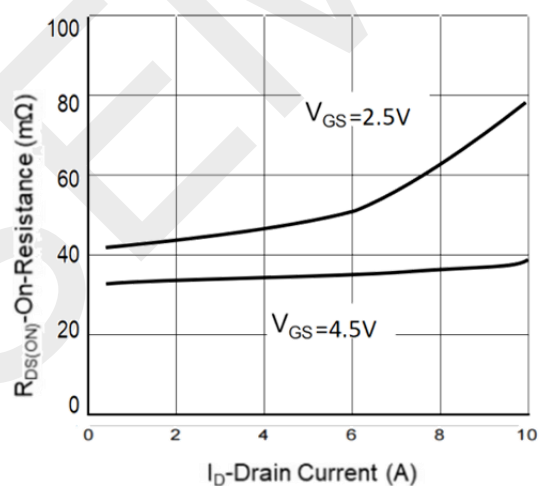
T_J -Junction Temperature (°C)

Normalized Threshold Voltage Vs. Temperature



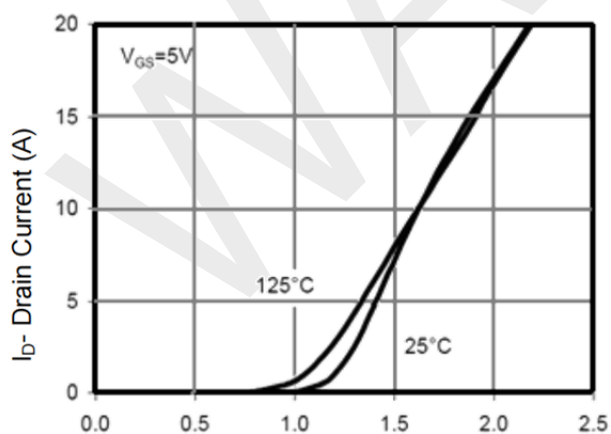
V_{DS} Drain-Source Voltage (V)

Typical Transfer Characteristics



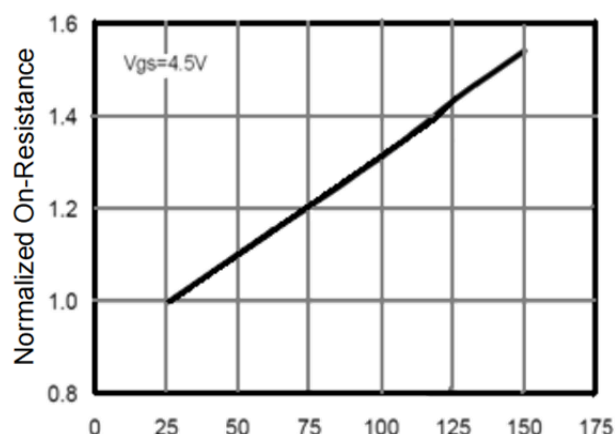
I_D -Drain Current (A)

Drain -Source Voltage vs Gate -Source Voltage



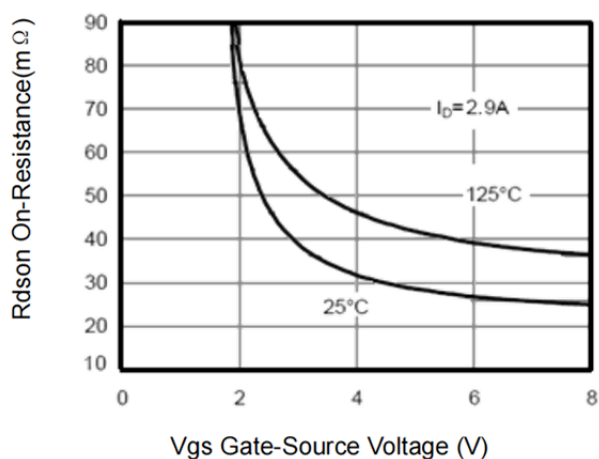
V_{GS} Gate-Source Voltage (V)

Typical Source-Drain Diode Forward Voltage

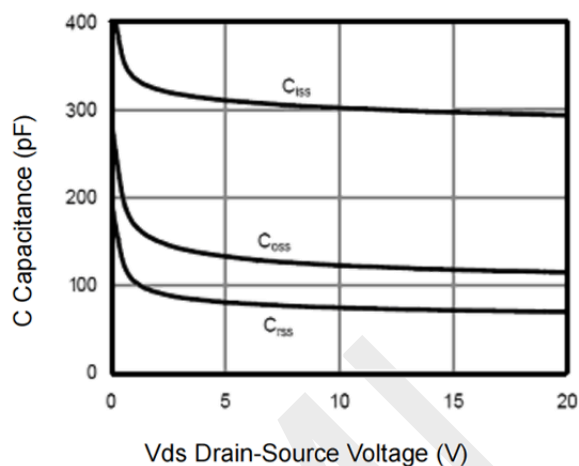


T_J -Junction Temperature (°C)

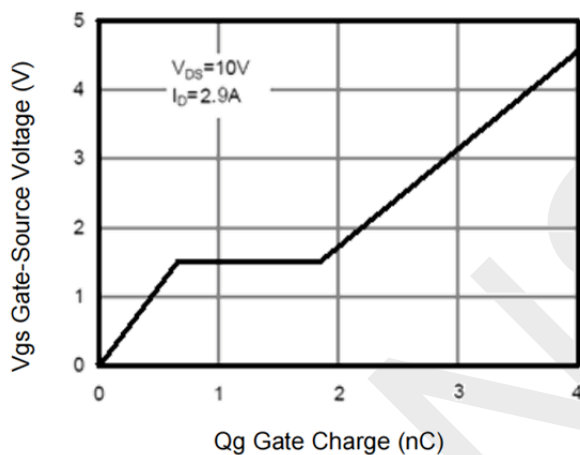
Maximum Safe Operating Area



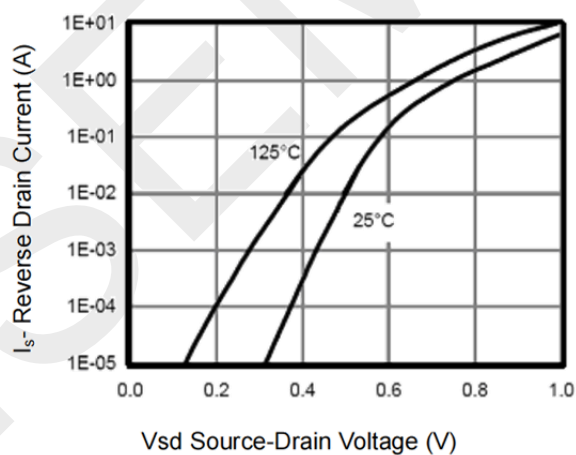
Typical Capacitance Vs. Drain-Source Voltage



Typical Gate Charge Vs. Gate-Source Voltage

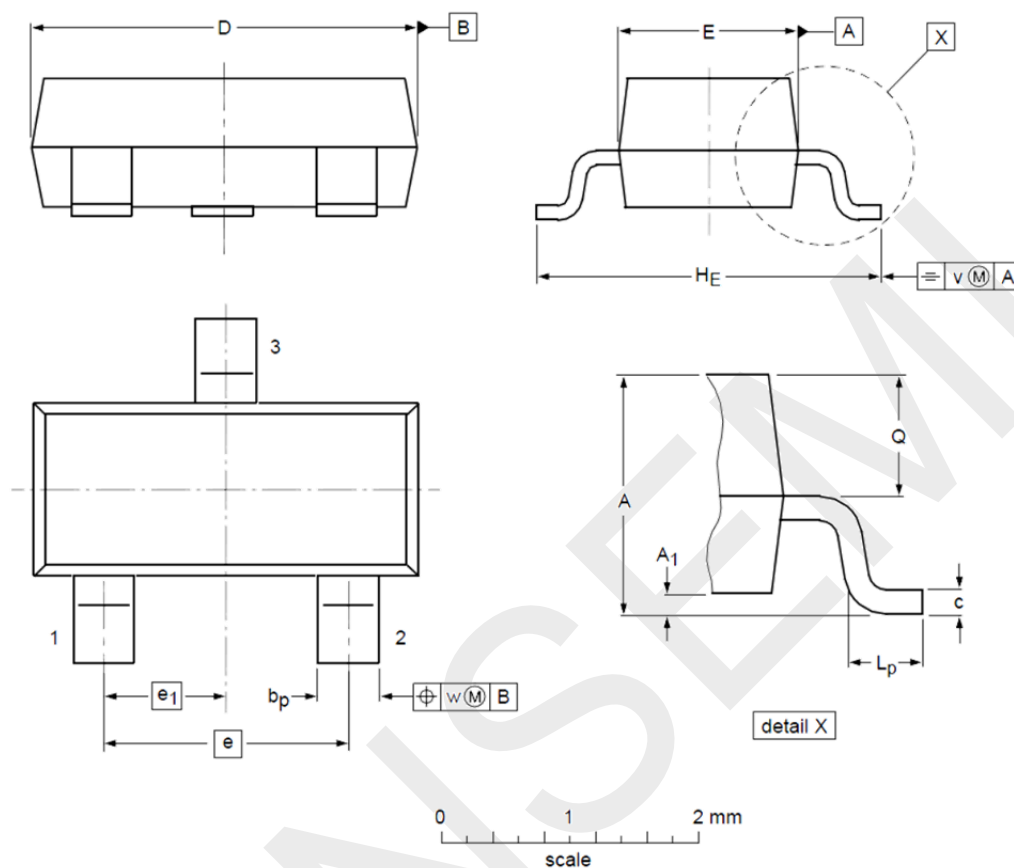


Typical Capacitance Vs. Drain-Source Voltage



Typical Gate Charge Vs. Gate-Source Voltage

7.Package Dimensions



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	1.00	1.17	1.30	A ₁	0.01	0.05	0.10
b _p	0.35	0.39	0.50	c	0.10	0.20	0.26
D	2.70	2.90	3.10	E	1.30	1.58	1.70
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.50	2.78	3.00	L _p	0.20	0.32	0.60
Q	0.23	0.27	0.33	v	--	0.20	--
w	--	0.20	--				

8.Important Notice

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